Electronic Supplementary Material (ESI) for Molecular Systems Design & Engineering.

Supporting information for

Flexible and Transparent Graphene Complementary Logic Gates

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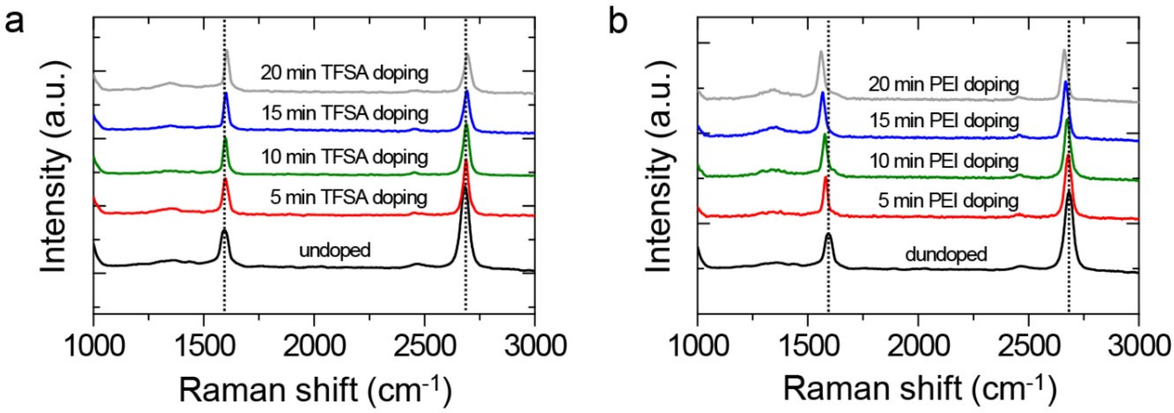

Figure S1. Raman spectra of graphene layer doped with (a) TFSA and (b) PEI for various doping times.

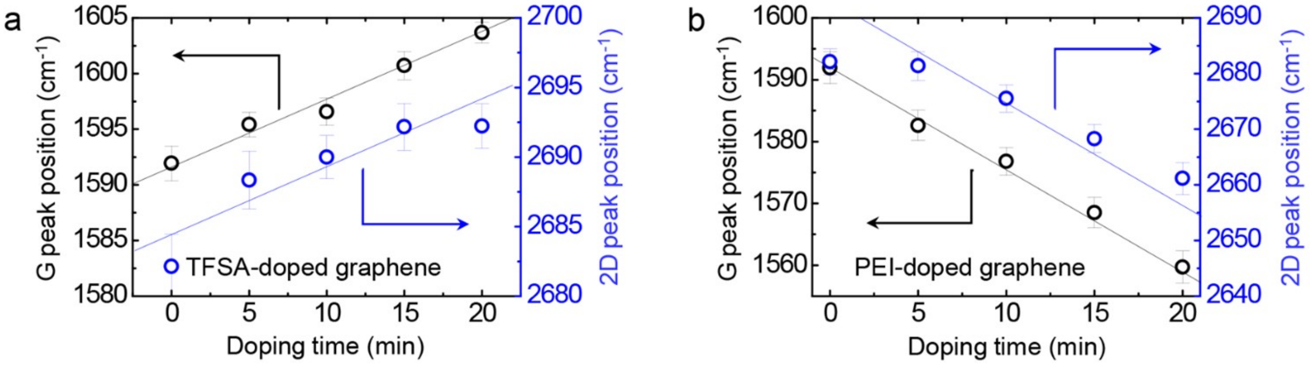

Figure S2. Variation of G and 2D band peak positions of graphene layer doped with (a) TFSA and (b) PEI for various doping times.

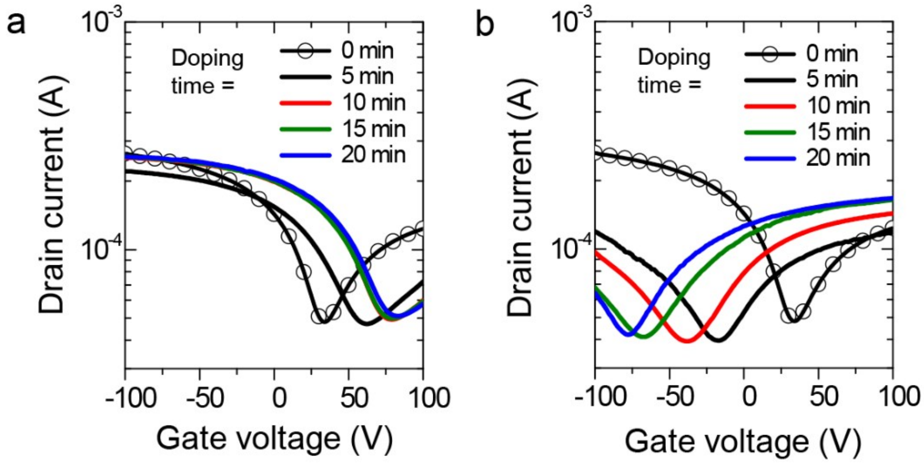

Figure S3. Transfer characteristics of the SiO_2-gated graphene transistor based on the graphene channel doped with (a) TFSA and (b) PEI for various doping times.